Silicon NPN Power Transistors BU546

DESCRIPTION

·With TO-3 package
·High voltage
·Fast switching speed

APPLICATIONS

·For color TV horizontal deflection circuits.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1300	V
V_{CEO}	Collector-emitter voltage	Open base	550	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		6	A
P_T	Total power dissipation	T_C=25□	100	W
T_j	Junction temperature		175	□
T_{stg}	Storage temperature		-65~175	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	1.0	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0;	550			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=10mA; I_C=0;	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3.2A;I_B=0.8A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3.2A;I_B=0.8A			1.3	V
I_{CBO}	Collector cut-off current	V_{CB}=1300V;I_E=0			1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V;I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=1.5A ; V_{CE}=5V	8			

PACKAGE OUTLINE

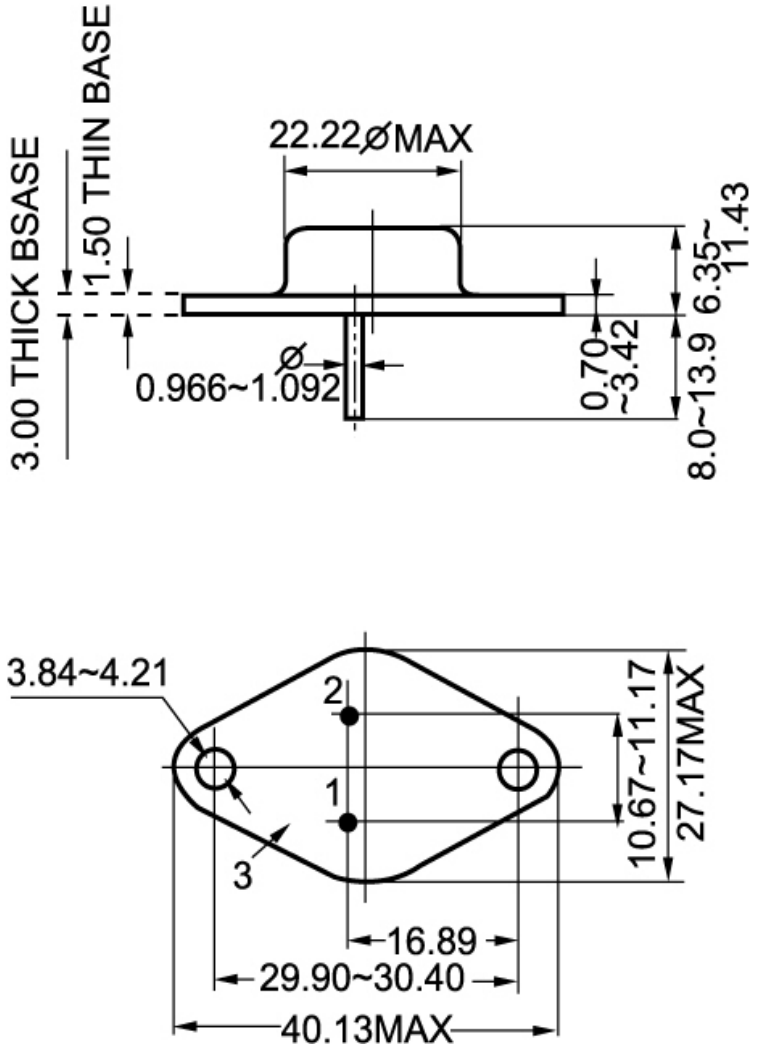

Fig.2 Outline dimensions